	Date
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	Experiment-1
іі ш ій	Objective :- To familiarize with electronic components and the usage of multimeter for the Measurement of resistance Classification of capacitors and measurement of their capacitance Diode testing Francistor testing Make voltage divides connection and verify its Thursin Model using various Apparatus Requised:- assangements of resistors Plastic circuit Board (PCB) Multimeter Probe.
ìv	Capacitor probe
٧.	Theory:
(i)	Measurement of Resistance: A presistor is a two-terminal electrical component that implement electric resistance as a circuit element. It opposes electric current by producing a voltage drop across its terminal in accordance with ohm's law R = V/I (for linear resistors). The four coloured bands on the four resistance and the permitted tolerance on the values of their resistance and the permitted tolerance on the values, in ohms. The first three bands (closest together) give the value of suistance in ohms (n). The band of the end first indicates the fravious significant digit(n,).

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	the second band indicates second digit (n2). The third
	band indicates the no of zeroes the following
	these two digits(n3). Bands are colour coded as follows:
	Colour Black Brown Red Orange Yellow Green Blue Violet Pares White
	Colour Black Brown Red Orange Yellow Green Blue Violet Grey White Digit 0 1 2 3 4 5 6 7 8 9
	8
	fourth band at the end indicates the tolerance. A red
	band means the resistor's value will be within ±2%
	of the stated value, gold + 5%, silver I 10%, and
	absence of fourth band indicates + 20%- tolerance.
	Identification of capacitors and measuring capacitors.
	V V
	Small capacitors:
	Tantalum: Thes are often coloured arrinders.
	Tantalum: Thes are often coloured cylinders. Mylar: Yellow coloured cylinders made of long coils of metal foils separated by thin dielectrics.
	foils separated by thin dielectrics
	Ceranics- Disc shaped
	Dide Testing: It potential lies diff. lies around 0.6 mu,
,	then it is a Si disde, and it between 0.3-0.4 mu, then
	it is Ge diode
	Transistor for testing: Fransistor is three terminal device
	with collector (c), Base (B), emitter (E) If multimeter trans
	display reading when the B is connected to anode
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	then B is p-type and hance transistor is non type.
	If multimeter displays rading when B is connected to
	cottade, then B is n-type and transistor is pop type
	g , .
	1
	Dispression: (By Uselin Rategia >16 05/190/13/)
	In the board identify the circuit shown.
	What is the resistance between terminals To 4 To?
	Measure the resistance and theory by verifying that the
	bottom ends of R2 4 R3 are electrically joined
(i)	In fig(i),
	Resistance between T3 4 T7 = 9.14 KD (by multimeta)
	Resistance between 5 1 Tz by calculation
	Reg = R, + R2+R3 = 4.89 +2.4+2.34
	= 9,63 KJ2
	Hence bottom ends of R2 and R3 are electrically jained.
0-2	Will the resistance blu T3 4T7 differ if the ground
	points are instead actually connected to some point
	is planot carth?
	No, because the potential of cont differente between
•	two points is 0 as they are connected to same point to
	eputh.
•	
W-3	Measure the applied voltage VTs at T3. Verify that the
	voltage VT4 at T4 is given by

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Vout = $Vin \times R_2$ $R_1 + R_2$,
Sol- In fig(iii) Vin = $Vt_3 = \frac{12}{12}$ 12.12 V By multimeter, $Vt_4 = 3.89$ V	
By calculating, $V_{Ty} = \frac{12.12 (R_2)}{R_1 + R_2} = \frac{12.12 (R_3)}{R_2} = \frac{12.12 (R_3)}{R_2} = \frac{12.12 (R_3)}{R_3} = 12.12 (R$	2.4KS2 3.95V 3 KS2
0- what are Rin and Rout in fig(iv)? Rin = R ₁ + R ₂ = 7.29kn Rout = R ₁ R ₂ = R ₁ R ₂ Y ₂ R ₃ Y ₂ · Y ₂ O R ₁ +R ₂ 7.29	KD = 1.609 KD
(a) when $R_1 = R_3$ $R_2 = R_3 = 2.34 \text{ KD}$	in Lig(v) wing
By calculation, $V_{L} = Vin \times R_{2}R_{L} = 2.34$) $\begin{pmatrix} R_{2}R_{1} + R_{1} \\ R_{2}+R_{L} \end{pmatrix} = 1 \text{ mA} \qquad \begin{bmatrix} R_{1} \\ R_{2} \end{bmatrix}$ R_{L}	y calculation)
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b R_= R_y=10.08, V_ = 3.37V (By multimater	
Calculated $V_1 = V_1 = V_1 D_1 \times R_2$ $\left(\frac{R_2 R_4 + R_1}{R_2 + R_4}\right) R_2$	2 Ry = 3.44 L+ Ry
H==	
IL = VL = 1.754 mA	(by calculation)
(c) When Rt = R3 11 Ry = 1.899 ks VL = 2.10V	(By multimoter)
$\frac{V_1 - V_1 h}{\left(\frac{R_2 R_1}{R_2 + R_1}\right)} \times \frac{R_2 R_1}{R_2 + R_1} = 12 \times .1$	78
* · · · · · · · · · · · · · · · · · · ·	calculation)
IL= VL 1.1268 mA	
I when capacitor is parallel to R _L , a R _L = R ₃ 11 Cb	
To steady state, capacitor act like an No cussont will from capacitor $V_{L} = 2.29 \text{V}$ (by multimater) $V_{L} = 2.29 \text{V}$	terning

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<u>b</u>	$I_{L} = 1 \text{ mA}$ $R_{L} = Ry 1 \text{ Cb}$ $V_{L} = 3.37 \text{ V (By multimeter)} V_{L} = 3.4 \text{ V (calculated)}$ $I_{L} = 1.754 \text{ mA}$
	The the
iii	Make the room In fig(vii) by applying +12V between Tig 4 ground and -12V between T20 4 ground. VA at T19 and compare with that given by VA= (V, R2+V2R1)/R1R
·	$\frac{V_1 - V_A}{R_1} = \frac{V_A - V_L}{R_2}$
	$V_1R_2 - V_1R_2 = V_1R_1 - V_2R_1$ $V_1R_2 - V_1R_2 + V_2R_1 - 12/2.40X + (Z_{12})(4.89)$ $R_1+R_2 - 240 + 4.89$
	By using multimeter, VA = -5.56 V
	By calculation, VA = 12/10 (2.4) -12 +2 (15-27 + -
	V = 12:10(15.27) - (11.95)(5.62) 15:183 V 15:27 + 8.62
	$V_{A} = 12.10(5-62) - 11.95(15-21) = -5.479V$ $15.27 + 5.62$

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DISCUSSION:	
ଓ ∀,	
	esastika Dutta
(10	30510060)
Rosistances are characterised by	the color bands. The value
of resistances are measured by co	lowe code and then with
multimetor, the mullimeter head	
by color codel.	•
,	
capacisons are can be of various	us lypes, eg: metallic polyester
jim s ceramic, electrolytic, etc. Simi	
the capacitances of the capacitous to	
it using the milimater in capac	•
capacilar probes.	
In experiment (ii), Ra and	Rs we joined by more-
Ku. FT bons ET Maninus pritiusies	
To and To is measured, we find it	
which further proves they are in a	
No, the resistance between t	
they are connected to some other p	- 1
measure the nex voltage difference	
-	
$\frac{\sqrt{V''}}{T_3} \frac{\sqrt{V''}}{R_1} \frac{\sqrt{V''}}{R_2} \frac{\sqrt{V''}}{R_3} \frac{\sqrt{V''}}{T_4} \frac{\sqrt{V''}}{\sqrt{V''}} = \frac{1}{2} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} = \frac{1}{2} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} = \frac{1}{2} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} \frac{\sqrt{V''}}{\sqrt{V''}} $	-v", + (v"-v") + (v'v_to)
= V4	

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on enperiment (iii) we measured ve and It across the toads wing both the multimeter and therein law there we we make that therein law holds have for this we with an applied DC voltage > W= 0. Hence, impedance = 1/10c = 00. Thus, it behaves like an open which and value of Ve remains some. On second parts of this experiment, we can apply kind that circuit kase: \[\frac{V_1 - V_A}{R_3} = \frac{V_A - V_A}{R_3} \] \[\frac{V_1 - V_A}{R_3} = \frac{V_A + V_A \text{R_3}}{R_3} \] This was also resified by the readings of the multimeter. Diodes are unitateral elements, i.e., they also parage of electricity in only one direction—forward bias. The semiconductor was in the diodes can be measured using the cutoff voltages (0 bmV for ST and 0.3-0.4mV for Germanium). Of thousa different resistances in different bias, and is generally used in forward bias. However special diods, like 2 enery diods, are used in backward bias.	np.	. 1 (0 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -
using both the multimeter and theurin law there we we moused that thevenin law holds bue for this circuit. In this experiment, we applied DC voltage > W= 0. Hence, impedance = 1/wc = 0. Hours, it behaves like an open circuit and value of V1 xemains same. In second part of this experiment, we can apply kirchoff's circuit tase: \[\frac{V_1 - VA}{R_3} = \frac{V_2 \times R_3}{R_3} \] \[\frac{V_1 - VA}{R_1 + R_2} = \frac{V_2 \times R_3}{R_1 + R_2} \] This was also verified by the readings of the multimeter, of electricity in only one direction—forward bias. The semiconductor were in the diodes can be measured using the cutoff voltages (Domv for SI and 0.3-0.4m v for Gremanium). It makes different resistances in different bias, and is generally used in forward bias. However special		
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withoff's circuit kap: \[\frac{V_1 - V_A}{R_1} = \frac{V_A - V_2}{R_3} \] \[\frac{P_1}{R_1 + R_2} \] \[\frac{P_1 + R_2}{R_1 + R_2} \] \[P_1 +	- 1	
NI-VA = VA-V2 R1 R3 => VA = (VIXR2+V2XR1) R1+R2 This was also rerified by the readings of the meetimeter. Diodes are unilateral elements, i.e., they allow persage of electricity in only one direction - forward bias. The semiconductor used in the diodes can be measured using the cutoff voltages (0.6mV for ST and 0.3-0.4mv for brownanium). St mans different resistances in different bias, and is generally used in forward bias. However special	0	en second part of this experiment, we can apply
This was also revisited by the readings of the multimeter. Diodes are unitarized elements, i.e., they allow parsage of electricity in only one direction - forward bias. The semiconductor used in the diodes can be measured using the cutoff voltages (Domy for SI and 0.3-0.4my for Germanium). Ot mans different resistances in different bias, and is generally used in forward bias. However special	1	wichoff's circuit kars:
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This was also rerified by the readings of the meetimeter. Diodes are unitateral elements, i.e., they allow passage of electricity in only one direction - forward bias. The semiconductor used in the diodes can be measured using the cutoff voltages (D.bMV for ST and 0.3-0.4mV for Germanium). Ot mans different resistances in different bias, and is generally used in forward bias. However special		R4 R3
Diodes are unilateral elements, i.e., they allow passage of electricity in only one direction - forward bias. The semiconductor used in the diodes can be measured using the cutoff voltages (0.6 mV for SI and 0.3-0.4 mV for Germanium). Ot mans different resistances in different bias, and is generally used in forward bias. However special		$= > VA = (V_1 \times R_2 + V_2 \times R_1)$ $R_1 + R_2$
of electricity in only one direction - Jorward bias. The semiconductor used in the diodes can be measured using the cutoff voltages (D.DMV for SI and 0.3-0.4mv for Gormanium). Ot mans different resistances in different bias, and is generally used in Jorward bias. However special	Ġ	This was also verified by the readings of the multimeter.
of electricity in only one direction - Jorward bias. The semiconductor used in the diodes can be measured using the cutoff voltages (D.DMV for SI and 0.3-0.4mv for Gormanium). Ot mans different resistances in different bias, and is generally used in Jorward bias. However special	D	iodes are unitateral elements, i.e., they allow passage
semiconductor used in the diodes can be measured using the cutoff voltages (0.6MV for SI and 0.3-0.4mv for Germanium). Ot mans different resistances in different bias, and is generally used in forward bias. However special		
the cutoff voltages (0.6MV for SI and 0.3-0.4m v for Germanium). Ot mans different resistances in different bias, and is generally used in forward bias. However special	يد	uniconductor used in the diodes can be measured using
and is generally used in forward bias. However special	₽	re cutoff voltages (0.6MV for SI and 0.3-0.4mv for
and is generally used in forward bigs. However special	- 61	
▼		· ·
diodes, like zoner diodes are used in backward bias.	1	4
	d	iodus, like zoner diodes are used in backward bigs.
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à junction transluter consists of Base, emitter and
allector. The base is sandwiched between the emitter and callector. They are broadly of two types- non and
pro.
The base is identified by testing all voltages a vion
combinations of volt terminals. It is the common point in the tests where there was voltage drop. Depending on
me prope, we then find whether it is p-n-p or n-p-n.
- Yne collector and emitter is distinguished by finding
voltage drop avons each in forward bias, such that:
8 K. Bapileodoy

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	Date
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1	lis cussion :-
	By Chelsi Raheja
	(IGCSIDOIŽ)
	An electric component is any basic discrete device or
Q	husical entity in an electronic system used to affect
0	lantons or their associated fields. Electronic components
1	are a number of electronic terminals which connect to
2	reality an electronic circuit with a partificial
	function like an amplifier or oscillator.
	Electionics components are classified as:
(i)	Active
ii. P	assive
	Electromechanic
	In the This experiment comprises measurement of
¥	existences value of resistors and capacitors which comes
	ender active class of electronic components and
<u>a</u>	us testing of diodes and transistors which
22	omes under passive class of electronic components.
М	tremustari prensituaem sinatule na di tI-Erstemithe
	which is used to measure circuit parameters like
	visistance, capacitance, voltage, diode tests, etc.
	Value of resistances can be obtained experimentally
bi	y colour bands that are drawn on a resistors.
-	
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which	ai some tolerance in
	value. Resistances and are also measured by
	meter which by connecting them across two
Joad	s connected to multimeter
	y connecting textropinals T3 and T7, we could
	that bottom ends of R2 and R3 are electrical
joined	as we could find that resistance
	on to be equal series
	tances of R, R2 and R3
Re	sistance between To and To does not differ
pecans	e threy do so ground points connected to
some	point of earth does not create as parential
	of benusua di Alias do alonjonist out assurted an
	o potential.
	periment (111) contained calculation of voltage land
	I using ohm's low and thereby
	sing it with direct values of Ve measured by
	Himeter which or comes by alm
ennal.	
-quu.	
Cor	paritors are characterized by capacitance values
	rollage ratings. Lapacitors may belong to
	nt families like ceramic, metallic, electrolytic,
etr we	e measured capacitances by using multimeter
and	by early wine a dillownt kind of prober
and	by pada using a different kind of probes
	also by using code
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Capacitor reactance is given by $X_{c=1}$ where we we wis angular frequency of source voltage A C is the capacitance, but for a DC source that we used in this experiment characterized w=0 which implies $x=\infty$ Therefore, a capacitor worked as an

open cixcuit, so when Cb is connected in parallel to

R, value of Vy remained the same.

By applying 12 V across T₁₈ and T₁₈ and -12V across T₂₀ and T₂₉ and ground, we verified voltage between Va and ground can be given by Va = (V₁R₂ + V₂R₁)/R₁+R₂ by comparing it with value measured by using multimeter across F₁A(t₁₉) and ground

Unilateral characteristic of diode, allows flow of current
in forward bias and voltage treated across them
can be used to find Semiconductor material which comes
sut to be 0.6 mV for silican and 0.3-0.4 mV for
Grennanium)

A transistor is a three terminal device which can be a p-n-p or n-pn by which can be determined by using multimeter in diade-check position and forward bias diade drops | VBE | >|VBC | which below to distinguish between collector and emitter sterminals with base is sandwiched between them. Some diades are used so in a reverse blased condition like zener diade to regulate voltage.

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